

TECHNICAL DATA DATA SHEET 4759, REV. A

# HERMETIC SCHOTTKY RECTIFIER Very Low Forward Voltage Drop

### Features:

- Soft Reverse Recovery at Low and High Temperature
- Very Low Forward Voltage Drop
- Low Power Loss, High Efficiency
- High Surge Capacity
- Guard Ring for Enhanced Durability and Long Term Reliability
- Guaranteed Reverse Avalanche Characteristics

## **Maximum Ratings**

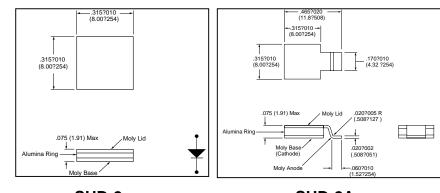
Characteristics	Symbol	Condition	Max.	Units
Peak Inverse Voltage	$V_{RWM}$	-	60	V
Max. Average Forward Current	$I_{F(AV)}$	50% duty cycle, rectangular wave form (Single)	60	А
Max. Average Forward Current	$I_{F(AV)}$	50% duty cycle, rectangular wave form (Common Cathode)	60	Α
Max. Peak One Cycle Non- Repetitive Surge Current	I <sub>FSM</sub>	8.3 ms, half Sine wave (per leg)	860	А
Non-Repetitive Avalanche Energy	E <sub>AS</sub>	$T_J = 25  ^{\circ}\text{C},  I_{AS} = 3.0  \text{A}, \\ L = 4.4  \text{mH (per leg)}$	20	mJ
Repetitive Avalanche Current	I <sub>AR</sub>	$I_{AS}$ decay linearly to 0 in 1 μs $f$ limited by $T_J$ max $V_A$ =1.5 $V_R$	3.0	А
Maximum Thermal Resistance	$R_{ ext{ hetaJC}}$	DC operation	0.35	°C/W
Max. Junction Temperature	TJ	-	-65 to +175	°C
Max. Storage Temperature	$T_{stg}$	-	-65 to +175	°C

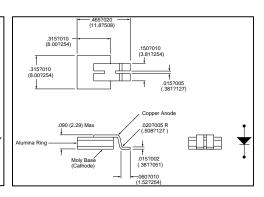
## **Electrical Characteristics**

Characteristics	Symbol	Condition	Max.	Units
Max. Forward Voltage Drop	V <sub>F1</sub>	@ 60A, Pulse, T <sub>J</sub> = 25 °C	0.66	V
(per leg)	V <sub>F2</sub>	@ 60A, Pulse, T <sub>J</sub> = 125 °C	0.59	V
Max. Reverse Current	I <sub>R1</sub>	@V <sub>R</sub> = 60V, Pulse,	1.2	mA
		T <sub>J</sub> = 25 °C		
(per leg)	I <sub>R2</sub>	$@V_R = 60V$ , Pulse,	90	mA
		T <sub>J</sub> = 125 °C		
Max. Junction Capacitance	C <sub>T</sub>	$@V_R = 5V, T_C = 25  ^{\circ}C$	2600	pF
(per leg)		$f_{SIG} = 1MHz,$		
		$V_{SIG} = 50 \text{mV (p-p)}$		

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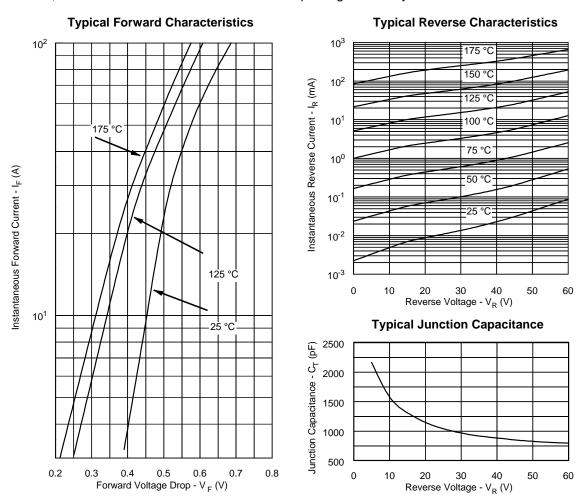
# **MECHANICAL DIMENSIONS: In Inches / mm**





SHD-2A SHD-2B

**Note:** The V<sub>f</sub> curves shown are for the SD200SB60 unpackaged die only.





#### **TECHNICAL DATA**

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